TwinDie™ DDR2 SDRAM

MT47H512M4 – 32 Meg x 4 x 8 Banks x 2 Ranks
MT47H256M8 – 16 Meg x 8 x 8 Banks x 2 Ranks

For the latest component data sheet, refer to Micron's Web site: www.micron.com

Functionality

The 2Gb (TwinDie™) DDR2 SDRAM uses Micron's 1Gb DDR2 monolithic die and, therefore, has similar functionality. This TwinDie data sheet is intended to provide a general description, package dimensions, and the ballout only. Refer to the Micron 1Gb DDR2 data sheet for complete information or for specifications not included in this document.

Features

- Uses 1Gb Micron die
- Two ranks (includes dual CS#, ODT, and CKE balls)
- Each rank has 8 internal banks for concurrent operation
- V_{DD} = $V_{DD}Q$ = +1.8V ±0.1V
- JEDEC-standard 63-ball ballout
- Low-profile package size 1.35mm MAX thickness

Options / Marking

	Marking
• Configuration	
– 32 Meg x 4 x 8 banks x 2 ranks	512M4
– 16 Meg x 8 x 8 banks x 2 ranks	256M8
• FBGA package (Pb-free)	
– 63-ball FBGA (9mm x 11.5mm)	THN
• Timing – cycle time[1]	
– 2.5ns @ CL = 5 (DDR2-800)	-25E
– 2.5ns @ CL = 6 (DDR2-800)	-25
– 3.0ns @ CL = 5 (DDR2-667)	-3
– 3.75ns @ CL = 4 (DDR2-533)	-37E
• Self refresh	
– Standard	None
• Operating temperature	
– Commercial (0°C ≤ T_C ≤ 85°C)	None
• Revision	:E

Notes: 1. CL = CAS (READ) latency.

Table 1: Key Timing Parameters

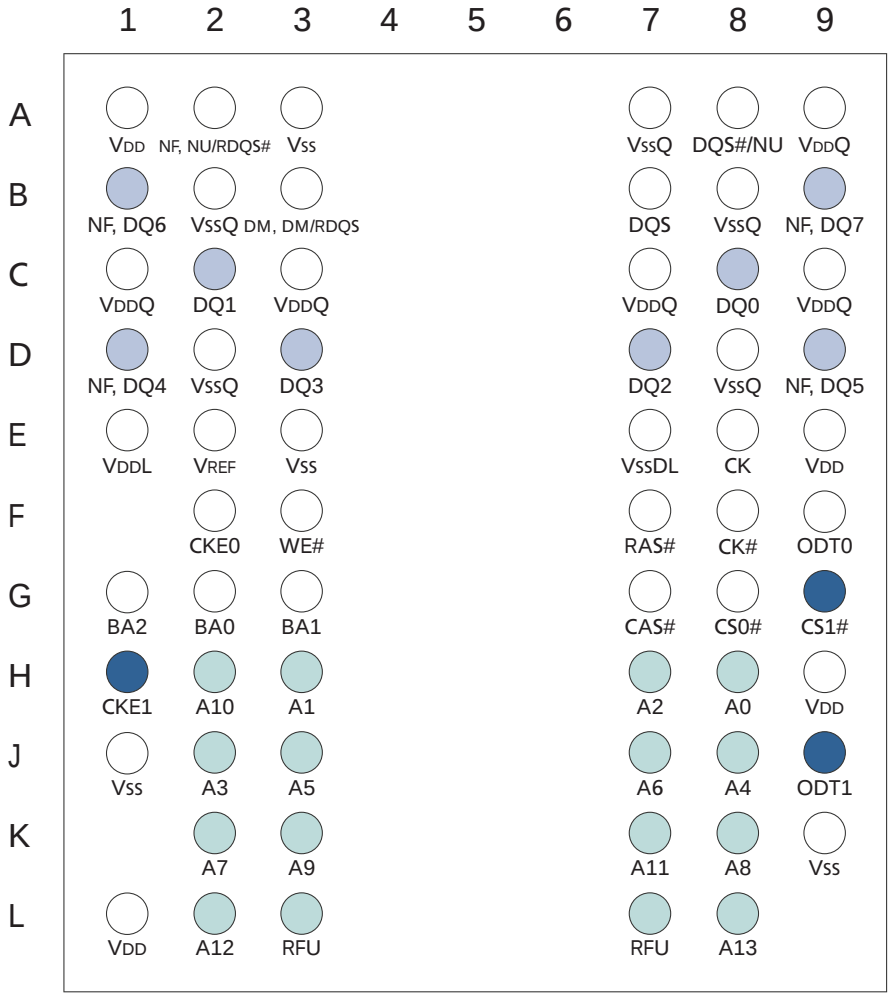
Speed Grade	Data Rate (MT/s)				^tRCD (ns)	^tRP (ns)	^tRC (ns)	^tRFC (ns)
	CL = 6	CL = 5	CL = 4	CL = 3				
-25E	–	800	533	–	12.5	12.5	55	127.5
-25	800	667	533	–	15	15	55	127.5
-3	–	667	533	400	15	15	55	127.5
-37E	–	–	533	400	15	15	55	127.5

Table 2: Addressing

Parameter	256 Meg x 8	512 Meg x 4
Configuration	16 Meg x 8 x 8 x 2	32 Meg x 4 x 8 x 2
Refresh count	8K	8K
Rank address	2 (CS0#–CS1#)	2 (CS0#–CS1#)
Bank address	8 (BA0–BA2)	8 (BA0–BA2)
Row address	16K (A0–A13)	16K (A0–A13)
Column address	1K (A0–A9)	2K (A0–A9, A11)

Ball Assignments and Descriptions

Figure 1: 63-Ball FBGA Assignments – x4, x8 (Top View)



Notes: 1. Dark balls designate balls that differ from the monolithic versions.

Table 3: 63-Ball FBGA Ball Descriptions – x4, x8

Ball Numbers	Symbol	Type	Description
H8, H3, H7, J2, J8, J3, J7, K2, K8, K3, H2, K7, L2, L8	A0, A1, A2, A3, A4, A5, A6, A7, A8, A9, A10, A11, A12, A13	Input	**Address inputs:** Provide the row address for ACTIVE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one bank (A10 LOW, bank selected by BA0–BA2) or all banks (A10 HIGH). The address inputs also provide the op-code during a LOAD MODE command.
G2, G3, G1	BA0, BA1, BA2	Input	**Bank address inputs:** BA0–BA2 define the bank to which an ACTIVE, READ, WRITE, or PRECHARGE command is being applied. BA0–BA2 define which mode register including MR, EMR, EMR(2), and EMR(3) is loaded during the LOAD MODE command.
E8, F8	CK, CK#	Input	**Clock:** CK and CK# are differential clock inputs. All address and control input signals are sampled on the crossing of the positive edge of CK and the negative edge of CK#. Output data (DQ, DQS, and DQS#) are referenced to the crossings of CK and CK#.
F2, H1	CKE0, CKE1	Input	**Clock enable:** CKE enables (registered HIGH) and disables (registered LOW) the internal circuitry and clocks on the DDR2 SDRAM.
G8, G9	CS0#, CS1#	Input	**Chip select:** CS# enables (registered LOW) and disables (registered HIGH) the command decoder. All commands are masked when CS# is registered HIGH. CS# provides for external rank selection on systems with multiple ranks. CS# is considered part of the command code.
B3	DM	Input	**Input data mask:** DM is an input mask signal for write data. Input data is masked when DM is sampled HIGH along with the input data during a write access. DM is sampled on both edges of DQS. Although DM balls are input-only, the DM loading is designed to match that of the DQ and DQS balls.
F9, J9	ODT0, ODT1	Input	**On-die termination:** ODT enables (registered HIGH) and disables (registered LOW) termination resistance internal to the DDR2 SDRAM. When enabled, ODT is only applied to each of the following balls: DQ0–DQ7, DQS, DQS#, and DM. The ODT input will be ignored if disabled via the LOAD MODE command.
F7, G7, F3	RAS#, CAS#, WE#	Input	**Command inputs:** RAS#, CAS#, and WE# (along with CS#) define the command being entered.
C8, C2, D7, D3	DQ0, DQ1, DQ2, DQ3	I/O	**Data input/output:** Bidirectional data bus for the x4 configuration.
C8, C2, D7, D3, D1, D9, B1, B9	DQ0, DQ1, DQ2, DQ3, DQ4, DQ5, DQ6, DQ7	I/O	**Data input/output:** Bidirectional data bus for the x8 configuration.
A8, B7	DQS#, DQS	I/O	**Data strobe:** Output with read data. Edge-aligned with read data. Input with write data for source-synchronous operation. Center-aligned with write data. DQS# is only used when differential data strobe mode is enabled via the LOAD MODE command.
A2, B3	RDQS#, RDQS	I/O	**Redundant data strobe:** For the x8 configuration only. RDQS is enabled/disabled via the LOAD MODE command to the extended mode register (EMR). When RDQS is enabled, RDQS is output with read data only and is ignored during write data. When RDQS is disabled, B3 becomes data mask (see DM ball). RDQS# is only used when both RDQS and the differential data strobe mode are enabled.
A1, E9, H9, L1	V_{DD}	Supply	**Power supply:** 1.8V ±0.1V.

Table 3: 63-Ball FBGA Ball Descriptions – x4, x8 (continued)

Ball Numbers	Symbol	Type	Description
E1	$V_{DD}L$	Supply	**DLL power supply:** 1.8V ±0.1V.
A9, C1, C3, C7, C9	$V_{DD}Q$	Supply	**DQ power supply:** 1.8V ±0.1V. Isolated on the device for improved noise immunity.
E2	V_{REF}	Supply	SSTL_18 reference voltage ($V_{DD}Q/2$).
A3, E3, J1, K9	V_{SS}	Supply	Ground.
E7	$V_{SS}DL$	Supply	**DLL ground:** Isolated on the device from V_{SS} and $V_{SS}Q$.
A7, B2, B8, D2, D8	$V_{SS}Q$	Supply	**DQ ground:** Isolated on the device for improved noise immunity.
A2, B1, B9, D1, D9	NF	–	**No function:** These balls provide no function on the x4 configuration only.
A2, A8	NU	–	**Not used:** For the x8 configuration only. If EMR(E10) = 0, A2 is RDQS# and A8 is DQS#. If EMR(E10) = 1, then A2 and A8 are not used.
L3, L7	RFU	–	**Reserved for future use:** Row address bits A14 and A15.

Functional Description

The 2Gb (TwinDie) DDR2 SDRAM is a high-speed, CMOS dynamic random access memory device containing 2,147,483,648 bits and is internally configured as two 8-bank 1Gb DDR2 SDRAM devices.

Although each die is tested individually within the dual-die package, some TwinDie test results may vary from a like-die tested within a monolithic die package.

Each DDR2 SDRAM die uses a double data rate architecture to achieve high-speed operation. The DDR2 architecture is essentially a 4*n*-prefetch architecture, with an interface designed to transfer two data words per clock cycle at the I/O balls. A single read or write access consists of a single 4*n*-bit-wide, one-clock-cycle data transfer at the internal DRAM core and four corresponding *n*-bit-wide, one-half-clock-cycle data transfers at the I/O balls.

Addressing of the TwinDie is identical to the monolithic device. Additionally, multiple chip selects select the desired rank.

This TwinDie data sheet is intended to provide a general description, package dimensions, and the ballout only. Refer to the Micron 1Gb DDR2 data sheet for complete information regarding individual die initialization, register definition, command descriptions, and die operation.

Functional Block Diagrams

Figure 2: Functional Block Diagram (32 Meg x 4 x 8 Banks x 2 Ranks)

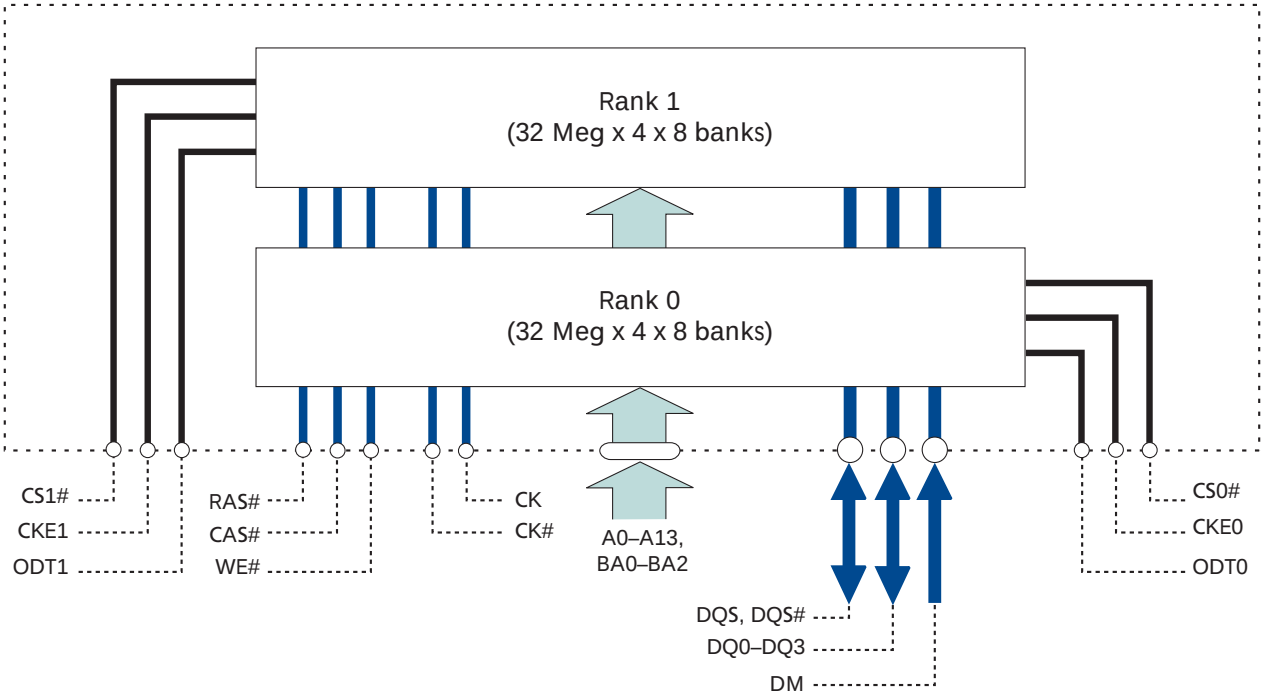
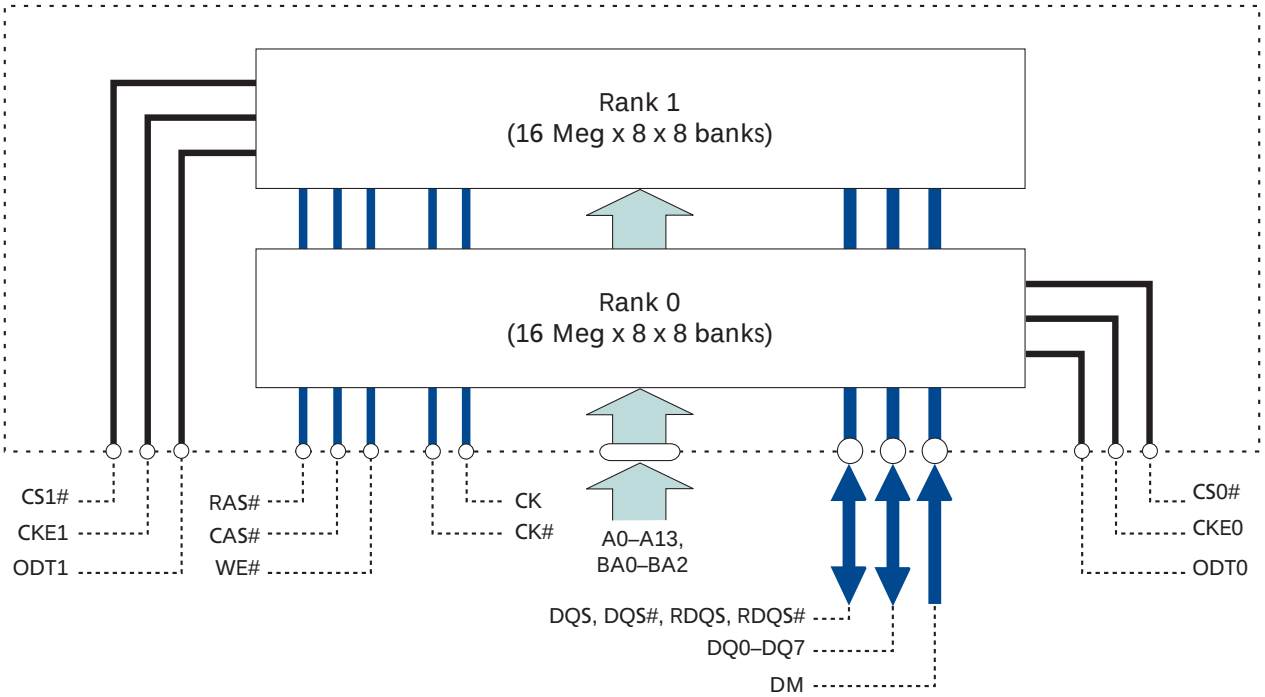


Figure 3: Functional Block Diagram (16 Meg x 8 x 8 Banks x 2 Ranks)



Electrical Specifications

Stresses greater than those listed in Table 4 may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions outside those indicated in the device data sheet is not implied. Exposure to absolute maximum rating conditions for extended periods may adversely affect reliability.

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Units	Notes
V_{DD}	V_{DD} supply voltage relative to V_{SS}	–1.0	+2.3	V	1
V_{DDQ}	V_{DDQ} supply voltage relative to V_{SSQ}	–0.5	+2.3	V	1, 2
V_{DDL}	V_{DDL} supply voltage relative to V_{SSL}	–0.5	+2.3	V	1
V_{IN}, V_{OUT}	Voltage on any ball relative to V_{SS}	–0.5	+2.3	V	3
I_I	Input leakage current; Any input 0V ≤ V_{IN} ≤ V_{DD}; All other balls not under test = 0V	–10	+10	µA	
I_{OZ}	Output leakage current; 0V ≤ V_{OUT} ≤ V_{DDQ}; DQ and ODT disabled	–10	+10	µA	
I_{VREF}	V_{REF} leakage current; V_{REF} = valid V_{REF} level	–4	+4	µA	

Notes:
1. V_{DD}, V_{DDQ}, and V_{DDL} must be within 300mV of each other at all times.
2. V_{REF} ≤ 0.6 × V_{DDQ}; however, V_{REF} may be ≥ V_{DDQ} provided that V_{REF} ≤ 300mV.
3. Voltage on any I/O may not exceed voltage on V_{DDQ}.

Temperature and Thermal Impedance

It is imperative that the DDR2 SDRAM device's temperature specifications, shown in Table 5 on page 8, be maintained to ensure the junction temperature is in the proper operating range to meet data sheet specifications. An important step in maintaining the proper junction temperature is using the device's thermal impedances correctly. Thermal impedances listed in Table 5 on page 8 apply to the current die revision and its packages.

Incorrectly using thermal impedances can produce significant errors. Read Micron technical note TN-00-08: "Thermal Applications," prior to using the thermal impedances in Table 6 on page 8. For designs that are expected to last several years and require the flexibility to use several DRAM die shrinks, consider using final target theta values (rather than existing values) to account for increased thermal impedances from the reduction in die size.

The DDR2 SDRAM device's safe junction temperature range can be maintained when the T_C specifications are not exceeded. In applications where the device's ambient temperature is too high, use of forced air and/or heat sinks may be required to satisfy the case temperature specifications.

Table 5: Temperature Limits

Symbol	Parameter	Min	Max	Units	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_C	Operating temperature – commercial	0	85	°C	2, 3

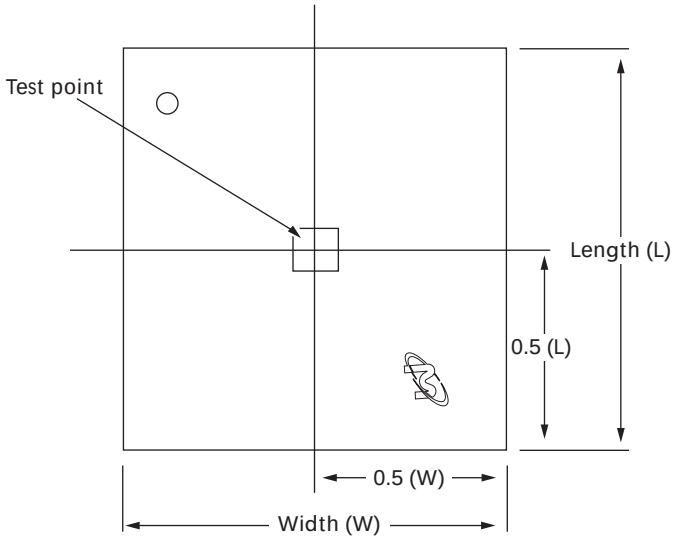
Notes:
1. Maximum storage case temperature; T_{STG} is measured in the center of the package, as shown in Figure 4. This case temperature limit is allowed to be exceeded briefly during package reflow, as noted in technical note TN-00-15: "Recommended Soldering Parameters," available on Micron's Web site.
2. Maximum operating case temperature; T_C is measured in the center of the package, as shown in Figure 4.
3. Device functionality is not guaranteed if the device exceeds maximum T_C during operation.

Table 6: Thermal Impedance

Die Rev	Package	Substrate	θ JA (°C/W) Airflow = 0m/s	θ JA (°C/W) Airflow = 1m/s	θ JA (°C/W) Airflow = 2m/s	θ JB (°C/W)	θ JC (°C/W)	Notes
E	63-ball	2-layer	56.8	42.3	36.5	26.1	3.9	1
		4-layer	42.1	33.9	30.4	25.6		
Last shrink target	63-ball	2-layer	62	46.1	39.8	28.5	4.3	2
		4-layer	45.9	37	33.2	27.9		

Notes:
1. Thermal resistance data is based on a number of samples from multiple lots and should be viewed as a typical number.
2. This is an estimate; simulated number and actual results may vary.

Figure 4: Temperature Test Point Location



Lmm x Wmm FBGA

IDD Specifications and Conditions

Table 7: DDR2 IDD Specifications and Conditions

Notes: 1–7 apply to the entire document; notes appear on page 10

Parameter/Condition	Combined Symbol	Individual Die Status	Bus Width	-25/ -25E	-3	-37E	Units
Operating one bank active-precharge current: ^{t}CK = ^{t}CK (IDD), ^{t}RC = ^{t}RC (IDD), ^{t}RAS = ^{t}RAS MIN (IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching (inactive die is in IDD2P condition, but with inputs switching)	IDD0	IDD0 = IDD0 + IDD2P + 5	x4, x8	102	97	82	mA
Operating one bank active-read-precharge current: IOUT = 0mA; Burst length (BL) = 4, CL = CL (IDD), AL = 0; ^{t}CK = ^{t}CK (IDD), ^{t}RC = ^{t}RC (IDD), ^{t}RAS = ^{t}RAS MIN (IDD), ^{t}RCD = ^{t}RCD (IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are switching; Data pattern is the same as IDD4W (inactive die is in IDD2P condition, but with inputs switching)	IDD1	IDD1 = IDD1 + IDD2P + 5	x4, x8	122	112	107	mA
Precharge power-down current: All banks idle; ^{t}CK = ^{t}CK (IDD); CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	IDD2P	IDD2P = IDD2P + IDD2P	x4, x8	14	14	14	mA
Precharge quiet standby current: All banks idle; ^{t}CK = ^{t}CK (IDD); CKE is HIGH, CS# is HIGH; Other control and address bus inputs are stable; Data bus inputs are floating	IDD2Q	IDD2Q = IDD2Q + IDD2P	x4, x8	57	47	47	mA
Precharge standby current: All banks idle; ^{t}CK = ^{t}CK (IDD); CKE is HIGH, CS# is HIGH; Other control and address bus inputs are switching; Data bus inputs are switching (inactive die is in IDD2P condition, but with inputs switching)	IDD2N	IDD2N = IDD2N + IDD2P + 5	x4, x8	62	52	52	mA
Active power-down current: All banks open; ^{t}CK = ^{t}CK (IDD); CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating (individual die status: IDD3P = IDD3P + IDD2P)	IDD3P	Fast PDN exit MR[12] = 0	x4, x8	47	37	37	mA
		Slow PDN exit MR[12] = 1	x4, x8	17	17	17	mA
Active standby current: All banks open; ^{t}CK = ^{t}CK (IDD), ^{t}RAS = ^{t}RAS MAX (IDD), ^{t}RP = ^{t}RP (IDD); CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching (inactive die is in IDD2P condition, but with inputs switching)	IDD3N	IDD3N = IDD3N + IDD2P + 5	x4, x8	72	67	57	mA
Operating burst write current: All banks open; Continuous burst writes; BL = 4, CL = CL (IDD), AL = 0; ^{t}CK = ^{t}CK (IDD), ^{t}RAS = ^{t}RAS MAX (IDD), ^{t}RP = ^{t}RP (IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching (inactive die is in IDD2P condition, but with inputs switching)	IDD4W	IDD4W = IDD4W + IDD2P + 5	x4	157	122	132	mA
			x8	172	147	137	

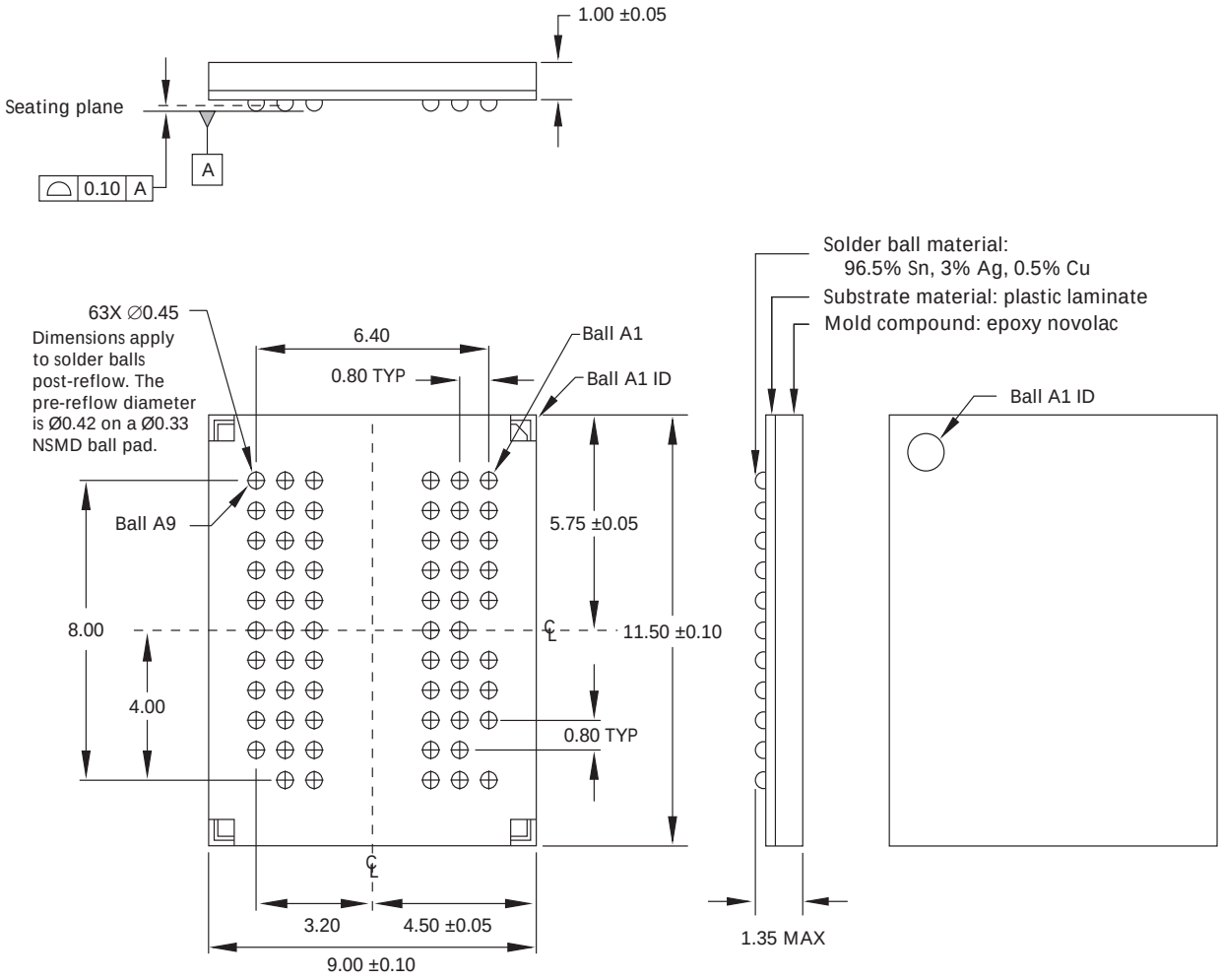
Table 7: DDR2 IDD Specifications and Conditions (continued)
Notes: 1–7 apply to the entire document; notes appear on page 10

Parameter/Condition	Combined Symbol	Individual Die Status	Bus Width	-25/ -25E	-3	-37E	Units
Operating burst read current: All banks open; Continuous burst reads; IOUT = 0mA; BL = 4, CL = CL (IDD), AL = 0; tCK = tCK (IDD), tRAS = tRAS MAX (IDD), tRP = tRP (IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching (inactive die is in IDD2P condition, but with inputs switching)	IDD4R	IDD4R = IDD4R + IDD2P + 5	x4	157	132	122	mA
			x8	172	147	137	
Burst refresh current: tCK = tCK (IDD); REFRESH command at every tRFC (IDD) interval; CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching (inactive die is in IDD2P condition, but with inputs switching)	IDD5	IDD5 = IDD5 + IDD2P + 5	x4, x8	247	227	222	mA
Self refresh current: CK and CK# at 0V; CKE ≤ 0.2V; Other control and address bus inputs are floating; Data bus inputs are floating	IDD6	IDD6 = IDD6 + IDD6	x4, x8	14	14	14	mA
Operating bank interleave read current: All banks interleaving reads; IOUT = 0mA; BL = 4, CL = CL (IDD), AL = tRCD (IDD) - 1 × tCK (IDD); tCK = tCK (IDD), tRC = tRC (IDD), tRRD = tRRD (IDD), tRCD = tRCD (IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are stable during deselects; Data bus inputs are switching (inactive die is in IDD2P condition, but with inputs switching)	IDD7	IDD7 = IDD7 + IDD2P + 5	x4, x8	347	292	282	mA

Notes:
1. IDD/IDD specifications are tested after the device is properly initialized. 0°C ≤ T_C ≤ +85°C. VDD = VDDQ = +1.8V ±0.1V; VDDL = +1.8V ±0.1V; VREF = VDDQ/2.
2. IDD/IDD parameters are specified with ODT disabled.
3. Data bus consists of DQ, DM, DQS, DQS#, RDQS, and RDQS#.
4. IDD/IDD values must be met with all combinations of EMR bits 10 and 11.
5. Definitions for IDD/IDD conditions:
   - 5a. LOW: VIN ≤ VIL(AC) MAX
   - 5b. HIGH: VIN ≥ VIH(AC) MIN
   - 5c. Stable: Inputs stable at a HIGH or LOW level
   - 5d. Floating: Inputs at VREF = VDDQ/2
   - 5e. Switching: Inputs changing between HIGH and LOW every other clock cycle (once per two clocks) for address and control signals
   - 5f. Switching: Inputs changing between HIGH and LOW every other data transfer (once per clock) for DQ signals, not including masks or strobes
6. IDD1, IDD4R, and IDD7 require EMR1, A12 to be enabled during testing.
7. IDD/IDD values reflect the combined current of both individual die. IDD*x* represents individual die values.

Package Dimensions

Figure 5: 63-Ball FBGA Package Dimensions



Notes: 1. All dimensions are in millimeters.

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